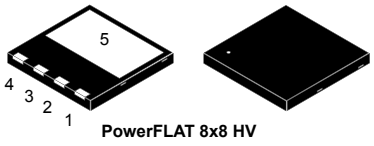
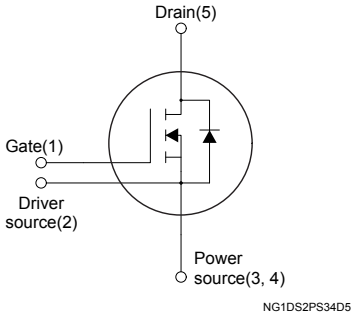
ST8L60N065DM9

Datasheet

N-channel 600 V, 51 mΩ typ., 39 A, MDmesh DM9 Power MOSFET in a PowerFLAT 8x8 HV package



PowerFLAT 8x8 HV



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
ST8L60N065DM9	600 V	65 mΩ	39 A

- Fast-recovery body diode
- Very low FOM ($R_{DS(on)}$•Q_g)
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggednes
- Excellent switching performance thanks to the extra driving source pin

Applications

- LLC resonant converter
- Power supplies and converters

Description

This N-channel Power MOSFET is based on the most innovative super-junction MDmesh DM9 technology, suitable for medium/high voltage MOSFETs featuring very low $R_{DS(on)}$ per area coupled with a fast-recovery diode. The silicon-based DM9 technology benefits from a multi-drain manufacturing process which allows an enhanced device structure. The fast-recovery diode featuring very low recovery charge (Q_{rr}), time (t_{rr}) and $R_{DS(on)}$ makes this fast-switching super-junction Power MOSFET tailored for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link
ST8L60N065DM9

Product summary	
Order code	ST8L60N065DM9
Marking	60N065DM9
Package	PowerFLAT 8x8 HV
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	39	A
	Drain current (continuous) at T_C = 100 °C	25	
I_{DM}(1)	Drain current (pulsed)	143	A
P_{TOT}	Total power dissipation at T_C = 25 °C	202	W
dv/dt(2)	Peak diode recovery voltage slope	120	V/ns
di/dt(2)	Peak diode recovery current slope	800	A/µs
dv/dt(3)	MOSFET dv/dt ruggedness	120	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 19.5 A, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 400 V.*
3. *V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 400 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.62	°C/W
R_{thJA}(1)	Thermal resistance, junction-to-ambient	45	°C/W

1. *When mounted on a standard 1 inch² area of FR-4 PCB with 2-oz copper.*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_J max.)	6	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 100 V)	521	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off-states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V	-	-	5	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)	-	-	200	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V	-	-	±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.5	4.0	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 19.5 A	-	51	65	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 400 V, f = 250 kHz, V_{GS} = 0 V	-	3350	-	pF
C_{oss}	Output capacitance		-	65	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{DS} = 0 to 400 V, V_{GS} = 0 V	-	650	-	pF
R_g	Intrinsic gate resistance	f = 250 kHz, open drain	-	0.5	-	Ω
Q_g	Total gate charge	V_{DD} = 400 V, I_D = 19.5 A, V_{GS} = 0 to 10 V (see the Figure 14. Test circuit for gate charge behavior)	-	66	-	nC
Q_{gs}	Gate-source charge		-	18.5	-	nC
Q_{gd}	Gate-drain charge		-	24	-	nC

1. *$C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to stated value.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 400 V, I_D = 19.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see the Figure 13. Switching times test circuit for resistive load and Figure 18. Switching time waveform)	-	24	-	ns
t_r	Rise time		-	7	-	ns
$t_{d(off)}$	Turn-off delay time		-	59	-	ns
t_f	Fall time		-	3.5	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	39	A
I_{SDM}(1)	Source-drain current (pulsed)		-	-	143	A
V_{SD}(2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 39 A	-	-	1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 39 A, di/dt = 100 A/µs, V_{DD} = 150 V (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	145	-	ns
Q_{rr}	Reverse recovery charge		-	1	-	µC
I_{RRM}	Reverse recovery current		-	12	-	A
t_{rr}	Reverse recovery time	I_{SD} = 39 A, di/dt = 100 A/µs, V_{DD} = 150 V, T_J = 150 °C (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	240	-	ns
Q_{rr}	Reverse recovery charge		-	2.7	-	µC
I_{RRM}	Reverse recovery current		-	20	-	A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

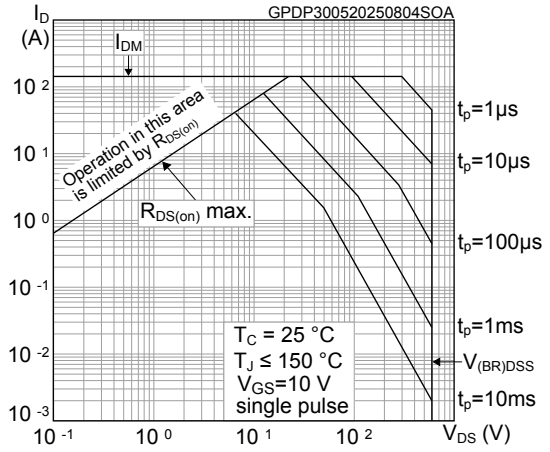


Figure 2. Maximum transient thermal impedance

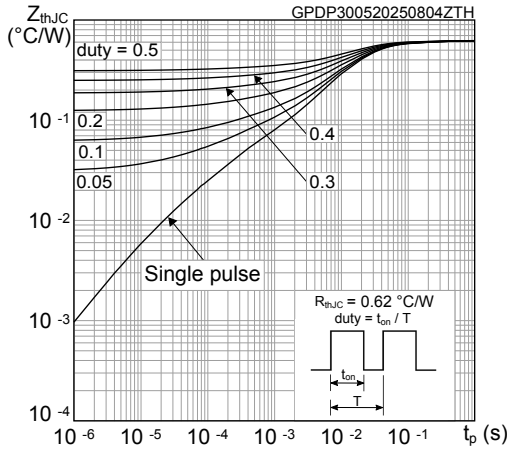


Figure 3. Typical output characteristics

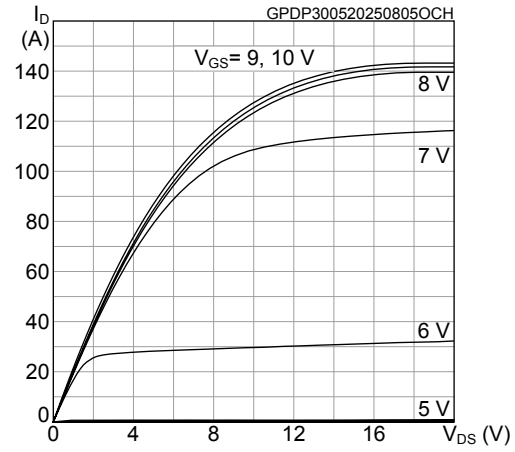


Figure 4. Typical transfer characteristics

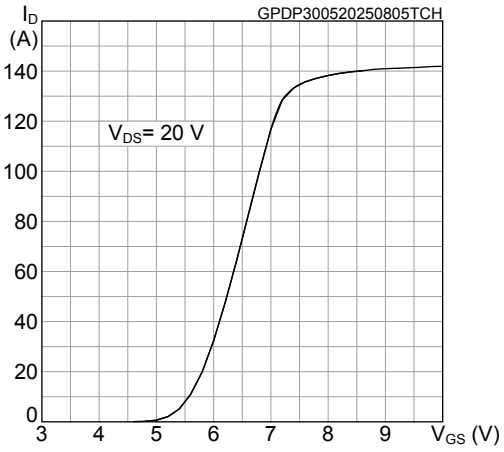


Figure 5. Typical gate charge characteristics

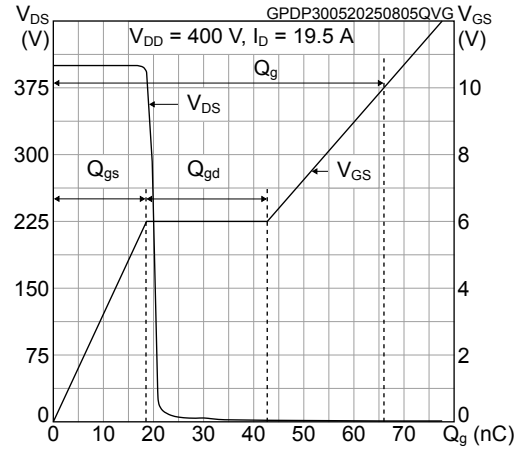


Figure 6. Typical drain-source on-resistance

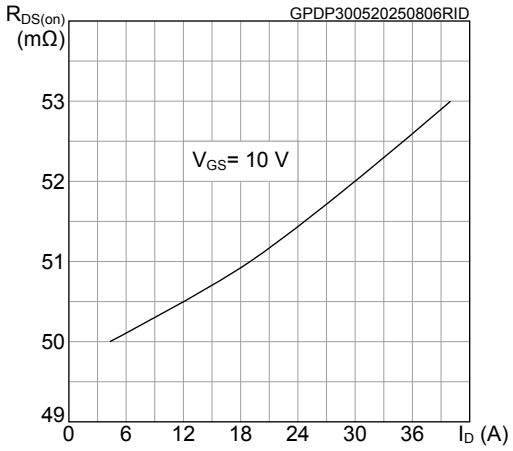


Figure 7. Typical capacitance characteristics

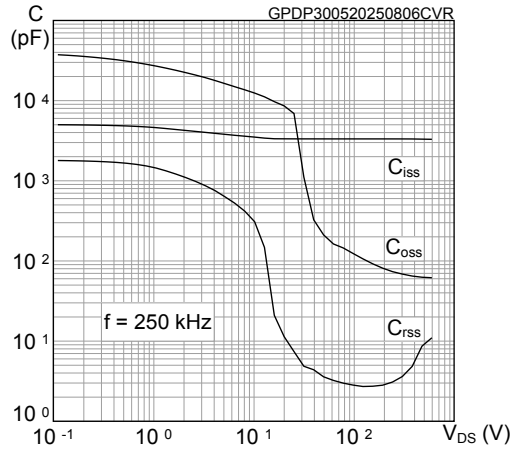


Figure 8. Typical output capacitance stored energy

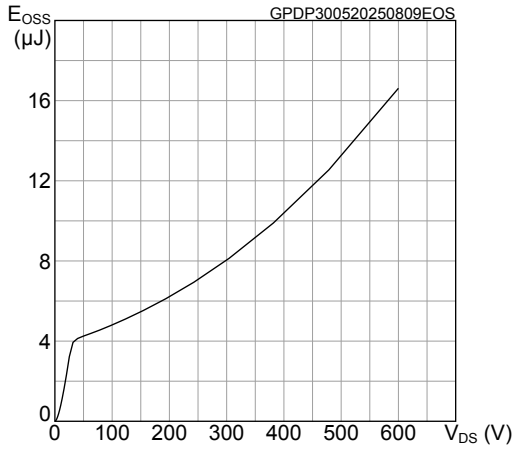


Figure 9. Normalized gate threshold vs temperature

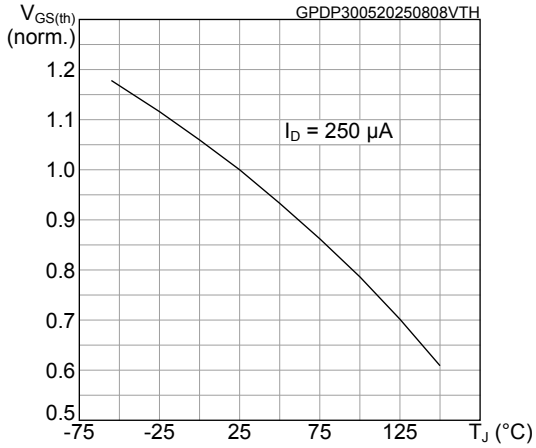


Figure 10. Normalized on-resistance vs temperature

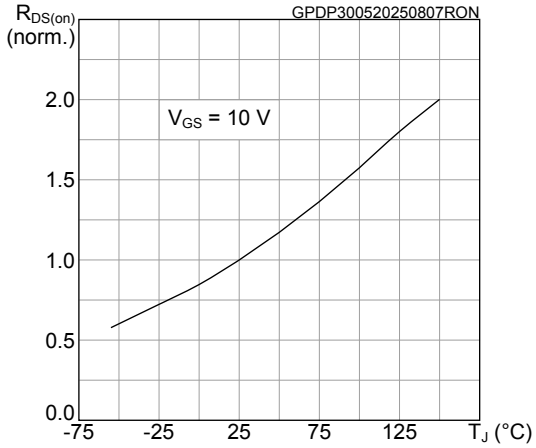


Figure 11. Normalized breakdown voltage vs temperature

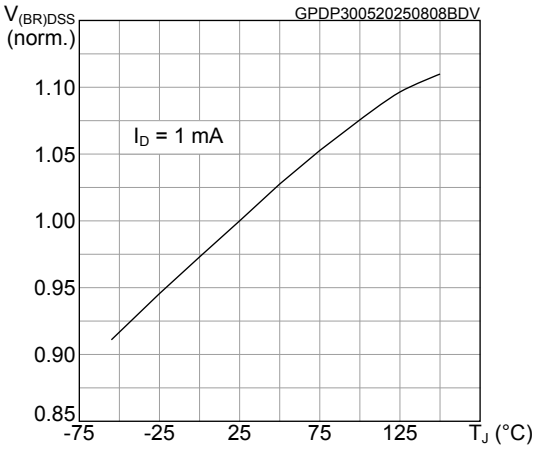
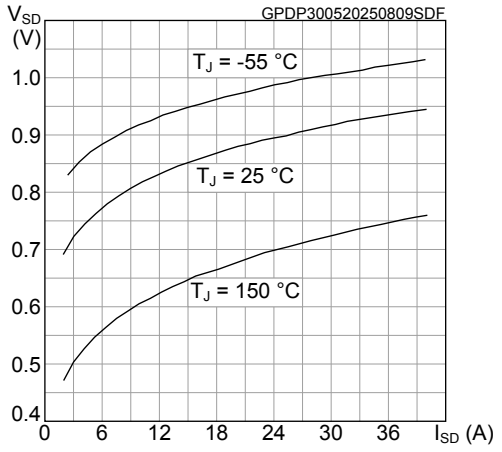


Figure 12. Typical reverse diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

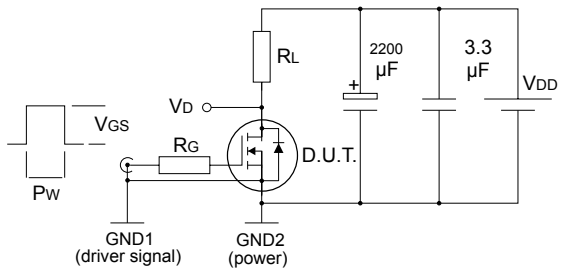


Figure 14. Test circuit for gate charge behavior

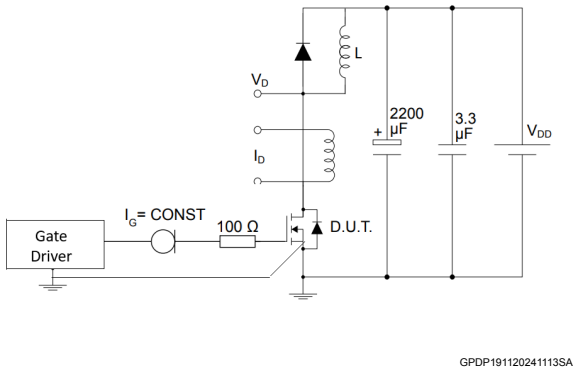


Figure 15. Test circuit for inductive load switching and diode recovery times

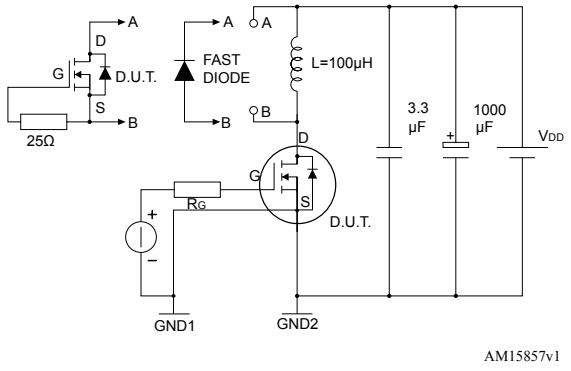


Figure 16. Unclamped inductive load test circuit

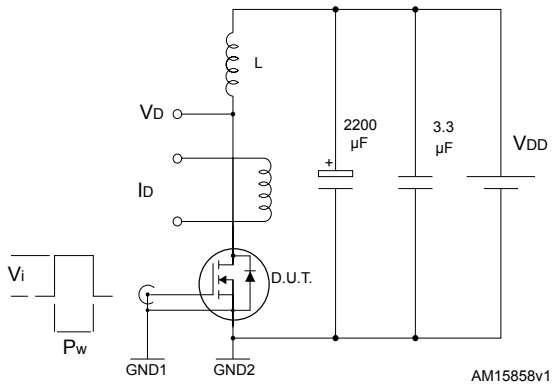


Figure 17. Unclamped inductive waveform

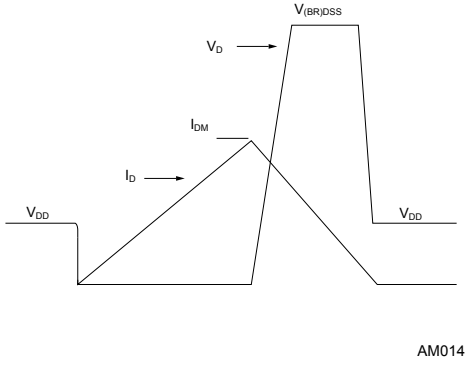
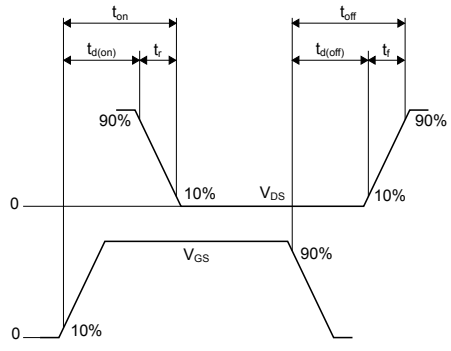


Figure 18. Switching time waveform



4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 PowerFLAT 8x8 HV type A package information

Figure 19. PowerFLAT 8x8 HV type A package outline

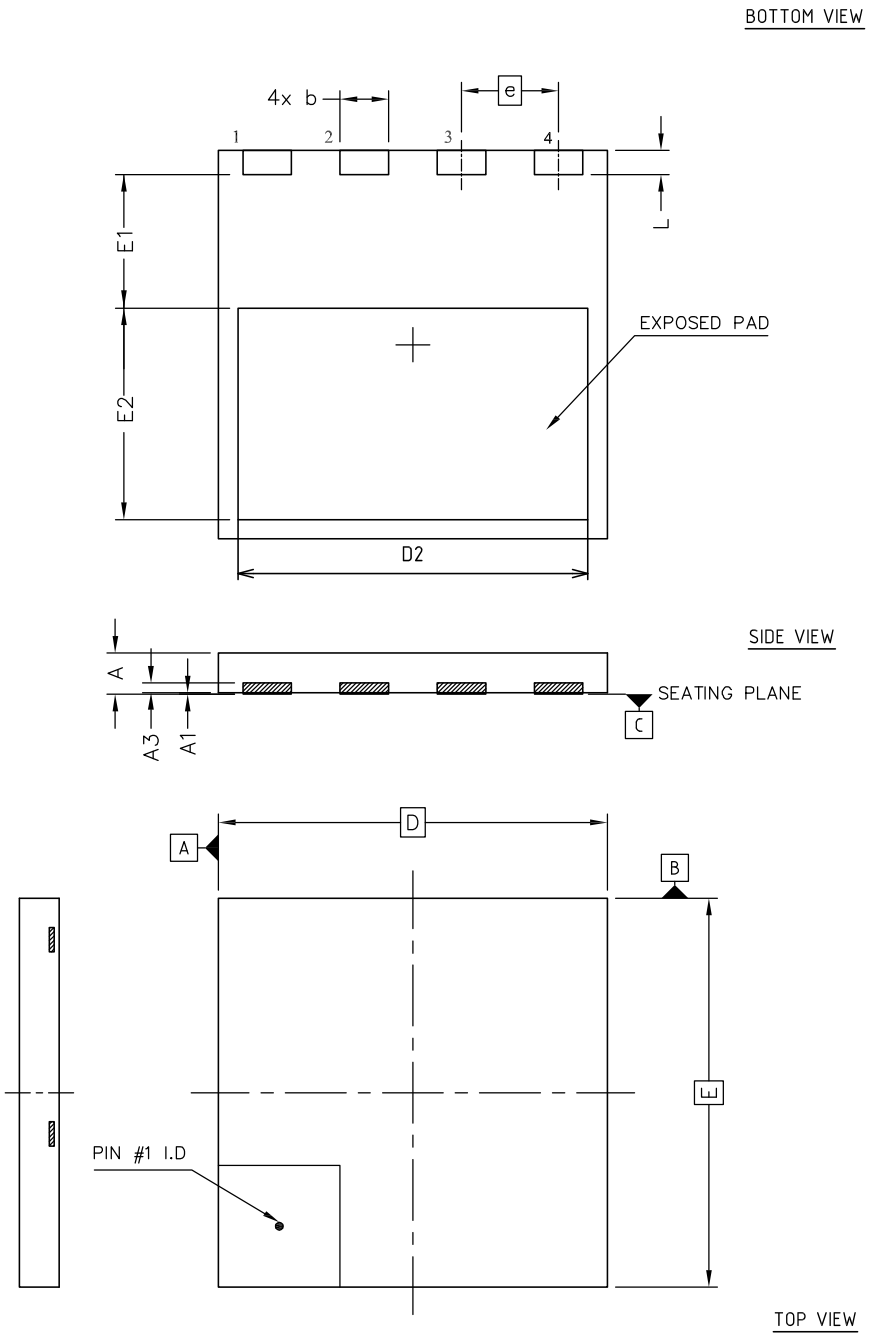
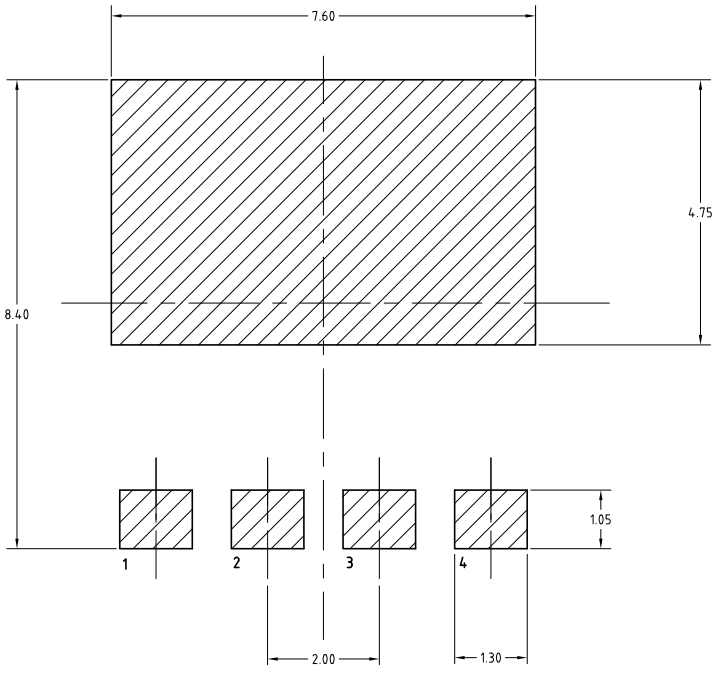


Table 8. **PowerFLAT 8x8 HV type A mechanical data**

Ref.	Dimensions (in mm)		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e		2.00 BSC	
L	0.40	0.50	0.60

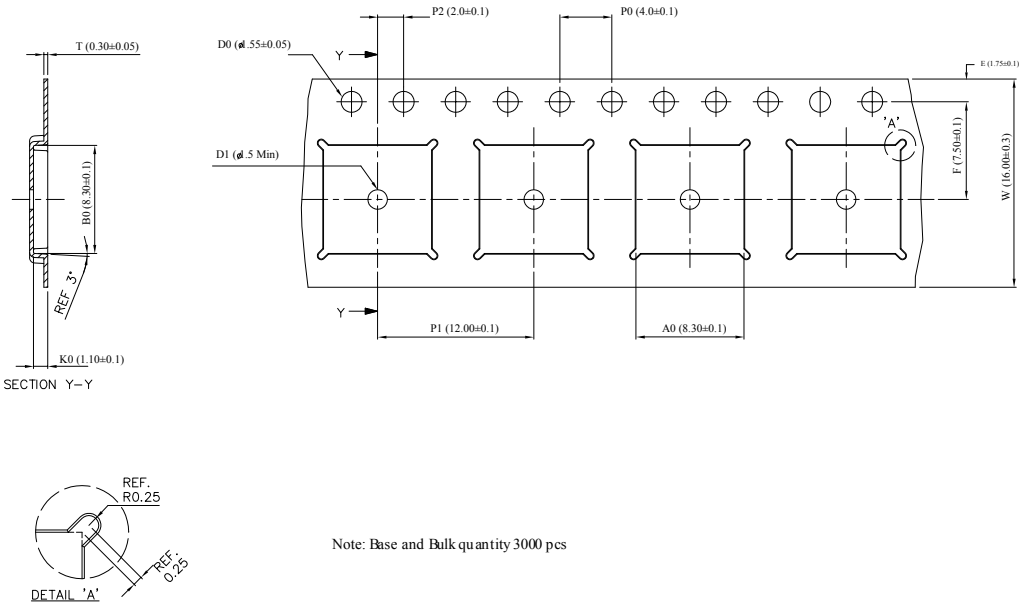
Figure 20. **PowerFLAT 8x8 HV footprint**



Note: All dimensions are in millimeters.

4.2 PowerFLAT 8x8 HV packing information

Figure 21. **PowerFLAT 8x8 HV tape**



Note: All dimensions are in millimeters.

Figure 22. **PowerFLAT 8x8 HV package orientation in carrier tape**

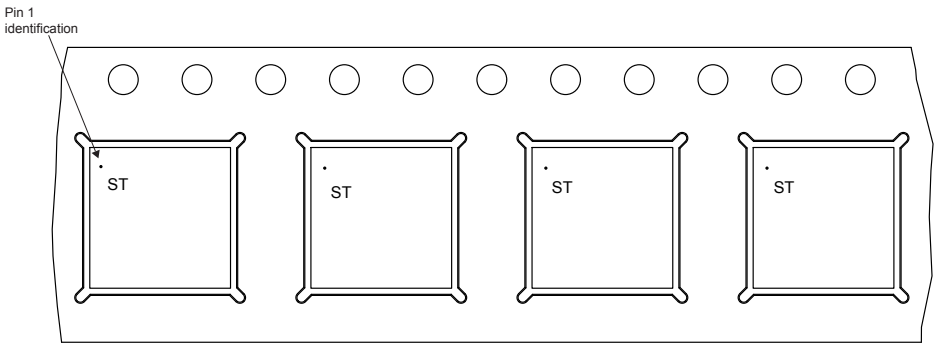
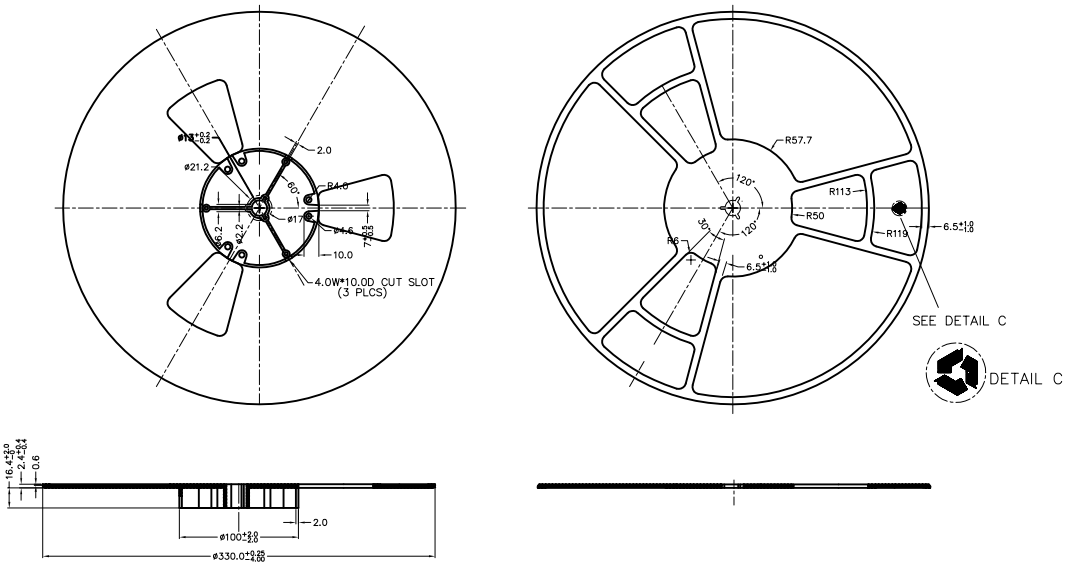


Figure 23. **PowerFLAT 8x8 HV reel**



Note: All dimensions are in millimeters.

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
04-Jun-2025	1	First release.

Contents

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